

# Liann-Be Chang

## List of Publications by Year in descending order

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57  
papers

667  
citations

686830

13  
h-index

610482

24  
g-index

58  
all docs

58  
docs citations

58  
times ranked

877  
citing authors

#	ARTICLE	IF	CITATIONS
1	A Surface Acoustic Wave Sensor with a Microfluidic Channel for Detecting C-Reactive Protein. <i>Chemosensors</i> , 2021, 9, 106.	1.8	8
2	Developing an Algorithm for Discriminating Oral Cancerous and Normal Tissues Using Raman Spectroscopy. <i>Journal of Personalized Medicine</i> , 2021, 11, 1165.	1.1	9
3	Annealing-Dependent Breakdown Voltage and Capacitance of Gallium Oxide-Based Gallium Nitride MOSOM Varactors. <i>Materials</i> , 2020, 13, 4956.	1.3	1
4	Novel Quantitative Analysis Using Optical Imaging (VELscope) and Spectroscopy (Raman) Techniques for Oral Cancer Detection. <i>Cancers</i> , 2020, 12, 3364.	1.7	9
5	Surface Acoustic Wave Sensor for C-Reactive Protein Detection. <i>Sensors</i> , 2020, 20, 6640.	2.1	17
6	The Improvement of Bonding Metal Layers in a GaAs Vertical Structure Light-Emitting Diode Package. <i>Journal of Electronic Materials</i> , 2020, 49, 6859-6864.	1.0	1
7	Effects of Annealing on Characteristics of Cu <sub>2</sub> ZnSnSe <sub>4</sub> /CH <sub>3</sub> NH <sub>3</sub> PbI <sub>3</sub> /ZnS/IZO Nanostructures for Enhanced Photovoltaic Solar Cells. <i>Nanomaterials</i> , 2020, 10, 521.	1.9	13
8	The Characteristics of Perovskite Solar Cells Fabricated Using DMF and DMSO/GBL Solvents. <i>Journal of Electronic Materials</i> , 2020, 49, 6823-6828.	1.0	13
9	Multiclass classification of autofluorescence images of oral cavity lesions based on quantitative analysis. <i>PLoS ONE</i> , 2020, 15, e0228132.	1.1	19
10	Capacitance Characteristics and Breakdown Mechanism of AlGaIn/GaN Metal-Semiconductor-Metal Varactors and their Anti-Surge Application. <i>Crystals</i> , 2020, 10, 292.	1.0	2
11	GaN 2DEG Varactor-Based Impulse Suppression Module for Protection Against Malicious Electromagnetic Interference. <i>Journal of Electronic Materials</i> , 2020, 49, 6798-6805.	1.0	2
12	Raman Spectroscopy Analysis for Optical Diagnosis of Oral Cancer Detection. <i>Journal of Clinical Medicine</i> , 2019, 8, 1313.	1.0	65
13	Reactive Mechanism of Cu <sub>2</sub> ZnSnSe <sub>4</sub> Thin Films Prepared by Reactive Annealing of the Cu/Zn Metal Layer in a SnSex + Se Atmosphere. <i>Crystals</i> , 2019, 9, 10.	1.0	14
14	Deep Etched Gallium Nitride Waveguide for Raman Spectroscopic Applications. <i>Crystals</i> , 2019, 9, 176.	1.0	2
15	Low-Cost CuIn <sub>1-x</sub> GaxSe <sub>2</sub> Ultra-Thin Hole-Transporting Material Layer for Perovskite/CIGSe Heterojunction Solar Cells. <i>Applied Sciences (Switzerland)</i> , 2019, 9, 719.	1.3	7
16	Meta-Learning Techniques to Analyze the Raman Data for Optical Diagnosis of Oral Cancer Detection. , 2019, , .		1
17	RGB-Stack Light Emitting Diode Modules with Transparent Glass Circuit Board and Oil Encapsulation. <i>Materials</i> , 2018, 11, 365.	1.3	2
18	Frequency dependent capacitance of metal semiconductor metal varactor diode and its tunable filter application. , 2018, , .		0

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19	Formation of Cl-Doped ZnO Thin Films by a Cathodic Electrodeposition for Use as a Window Layer in CIGS Solar Cells. <i>Materials</i> , 2018, 11, 953.	1.3	6
20	Deep traps in the ZnO nanorods/Si solar cells. <i>Journal of Alloys and Compounds</i> , 2017, 708, 247-254.	2.8	15
21	Lifetime of excess electrons in Cu <sup>2+</sup> Zn <sup>2+</sup> Sn <sup>2+</sup> Se powders. <i>Semiconductors</i> , 2017, 51, 18-22.	0.2	1
22	Phosphor-Free InGaN White Light Emitting Diodes Using Flip-Chip Technology. <i>Materials</i> , 2017, 10, 432.	1.3	9
23	Output Properties of Transparent Submount Packaged FlipChip Light-Emitting Diode Modules. <i>Applied Sciences (Switzerland)</i> , 2016, 6, 179.	1.3	2
24	Effect of Sn Content in a CuSnZn Metal Precursor on Formation of MoSe <sub>2</sub> Film during Selenization in Se+SnSe Vapor. <i>Materials</i> , 2016, 9, 241.	1.3	11
25	Thickness effect of IGZO layer in light-addressable potentiometric sensor. , 2016, , .		0
26	Effect of the chemical composition of Cu <sup>2+</sup> In <sup>3+</sup> Ga <sup>3+</sup> Se layers on the photoconductivity and conversion efficiency of CdS/CIGSe solar cells. <i>Semiconductors</i> , 2016, 50, 1344-1351.	0.2	1
27	The formation of MoSe <sub>2</sub> films during selenization process in CZTSe solar cells. , 2016, , .		0
28	Enhance the protection capability of intentional electro magnetic interference with Zinc Oxide sintered gas discharge tube. , 2015, , .		1
29	Improving Efficiency of Multicrystalline Silicon and CIGS Solar Cells by Incorporating Metal Nanoparticles. <i>Materials</i> , 2015, 8, 6761-6771.	1.3	40
30	Si/ZnO nanorods/Ag/AZO structures as promising photovoltaic plasmonic cells. <i>Journal of Applied Physics</i> , 2015, 117, .	1.1	17
31	Improved surge protection of flip-chip gallium nitride-based HEMTs by metal-semiconductor-metal two-dimensional electron gas varactor. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, 021401.	0.6	2
32	Capacitance Swing and Capacitance Ratio of GaN-Based Metal-Semiconductor-Metal Two-Dimensional Electron Gas Varactor with Different Dielectric Films. <i>Journal of Electrical Engineering and Technology</i> , 2015, 10, 1720-1725.	1.2	3
33	CZTSe solar cells prepared by electrodeposition of Cu/Sn/Zn stack layer followed by selenization at low Se pressure. <i>Nanoscale Research Letters</i> , 2014, 9, 678.	3.1	23
34	Tin sulfide thin films prepared by thermal evaporation and sulfurization. , 2014, , .		3
35	Bump and Underfill Effects on Thermal Behaviors of Flip-Chip LED Packages: Measurement and Modeling. <i>IEEE Transactions on Device and Materials Reliability</i> , 2014, 14, 161-168.	1.5	25
36	Comparison of silicone and spin-on glass packaging materials for light-emitting diode encapsulation. <i>Thin Solid Films</i> , 2014, 570, 496-499.	0.8	6

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37	Anomalous Decrease of Off-State Drain Leakage Current in GaN/AlGaIn HEMTs With Dual Optical Excitation. IEEE Electron Device Letters, 2014, 35, 820-822.	2.2	2
38	Highly sensitive palladium oxide thin film extended gate FETs as pH sensor. Sensors and Actuators B: Chemical, 2014, 205, 199-205.	4.0	122
39	Improving the reliability of eutectic bonding vertical power light-emitting diodes by a Mo buffer layer. Thin Solid Films, 2014, 570, 500-503.	0.8	4
40	Improvement of Surge Protection by Using an AlGaIn/GaN-Based Metal-Semiconductor-Metal Two-Dimensional Electron Gas Varactor. Japanese Journal of Applied Physics, 2012, 51, 124201.	0.8	4
41	Heat sink performances of GaN/InGaIn flip-chip light-emitting diodes fabricated on silicon and AlN submounts. Microelectronics Reliability, 2012, 52, 884-888.	0.9	19
42	Improvement of Surge Protection by Using an AlGaIn/GaN-Based Metal-Semiconductor-Metal Two-Dimensional Electron Gas Varactor. Japanese Journal of Applied Physics, 2012, 51, 124201.	0.8	5
43	An observation of charge trapping phenomena in GaN/AlGaIn/Gd <sub>2</sub> O <sub>3</sub> /Ni-Au structure. MOS schottky structure. , 2011, , .		0
44	Effect of Electron Leakage on Efficiency Droop in Wide-Well InGaIn-Based Light-Emitting Diodes. Applied Physics Express, 2011, 4, 012106.	1.1	30
45	An observation of charge trapping phenomena in GaN/AlGaIn/Gd <sub>2</sub> O <sub>3</sub> /Ni-Au structure. Applied Physics Letters, 2011, 98, .	1.5	14
46	Electrostatic Reliability Characteristics of GaN Flip-Chip Power Light-Emitting Diodes With Metal-Oxide-Silicon Submount. IEEE Transactions on Electron Devices, 2010, 57, 119-124.	1.6	11
47	Improvement of crystal quality of AlN grown on sapphire substrate by MOCVD. Crystal Research and Technology, 2010, 45, 703-706.	0.6	13
48	Fabrication and thermal analysis of flip-chip light-emitting diodes with different numbers of Au stub bumps. Microelectronics Reliability, 2010, 50, 683-687.	0.9	20
49	High-Efficiency InGaIn-Based Yellow-Green Light-Emitting Diodes. Japanese Journal of Applied Physics, 2010, 49, 021004.	0.8	14
50	Effects of Growth Parameters on Surface-morphological, Structural, Electrical and Optical Properties of AZO Films by RF Magnetron Sputtering. Materials Research Society Symposia Proceedings, 2009, 1201, 149.	0.1	0
51	Wideband double-ring resonator with transmission zeros and resonances using high permittivity aluminum nitride substrate. Microwave and Optical Technology Letters, 2009, 51, 2878-2882.	0.9	1
52	Lane detection system based on software and hardware codesign. , 2009, , .		3
53	The reflectivity of Mo/Ag/Au ohmic contacts on p-type GaN for flip-chip light-emitting diode (FCLED) applications. Applied Surface Science, 2008, 254, 4479-4482.	3.1	6
54	Effects of Growth Parameters on Surface-morphological, Structural and Electrical Properties of Mo Films by RF Magnetron Sputtering. Materials Research Society Symposia Proceedings, 2008, 1123, 18.	0.1	3

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55	Formation process of high reflective Ni <sup>+</sup> •Ag <sup>+</sup> •Au Ohmic contact for GaN flip-chip light-emitting diodes. Applied Physics Letters, 2007, 90, 163515.	1.5	33
56	The Reflectivity enhancement of Ni/Ag/(Ti or Mo)/Au Ohmic Contact for Flip-Chip Light-Emitting Diode Applications. , 2007, , .		0
57	Light Output Improvement of InGaN-Based Light-Emitting Diodes by Microchannel Structure. IEEE Photonics Technology Letters, 2007, 19, 1175-1177.	1.3	13